

EXHIBIT 15

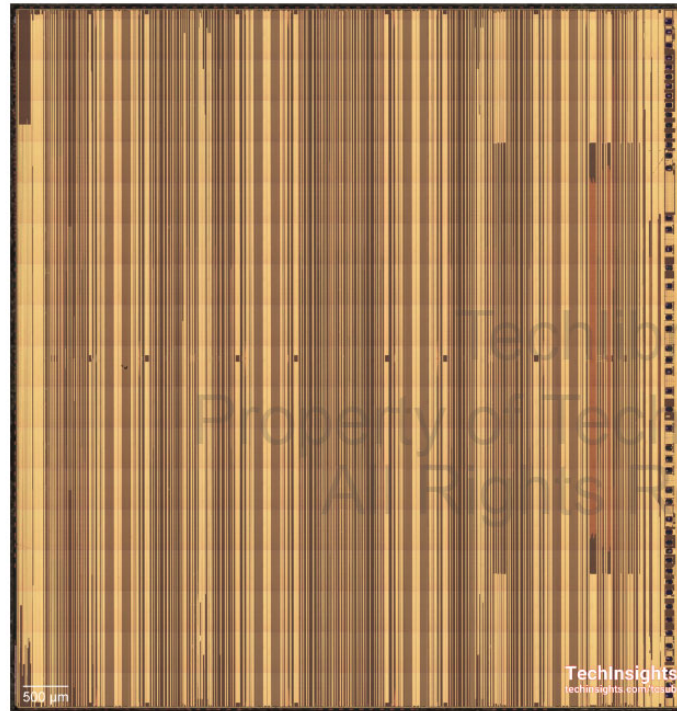
U.S. Patent No. 6,781,858

Claim 21	Identification: Lenovo Moto G Power mobile phone ¹									
21. A cubic memory array, comprising:	<div><div></div><div><div><div>moto g POWER</div><div>Go up to three days[†] on a single charge thanks to a 5000 mAh battery.</div><div>16MP triple camera system. Capture ultra-wide angle panoramas, sharper portraits, and super detailed close-up shots.</div><div>Dual Stereo Speakers tuned by Dolby[®].</div></div><div><table><tr><td>Operating system Android™ 10</td><td>Internal storage 64GB built-in^{††}</td><td>Sensors Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)</td></tr><tr><td>Processor Qualcomm® Snapdragon™ 665 Mobile Processor</td><td>Expandable Storage up to 512GB microSD card expandable^{†††}</td><td>Memory (RAM) 4GB</td></tr><tr><td colspan="3">Security Rear fingerprint reader</td></tr></table></div></div></div>	Operating system Android™ 10	Internal storage 64GB built-in ^{††}	Sensors Accelerometer, Gyroscope, Proximity, Ambient Light, Sensor Hub, Fingerprint reader, magnetometer (e-compass)	Processor Qualcomm® Snapdragon™ 665 Mobile Processor	Expandable Storage up to 512GB microSD card expandable ^{†††}	Memory (RAM) 4GB	Security Rear fingerprint reader		
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	<div><div>https://www.motorola.ca/smartphones-moto-g-power/p?skuId=13 https://www.gsmarena.com/motorola_moto_g_power-10076.php</div></div>									

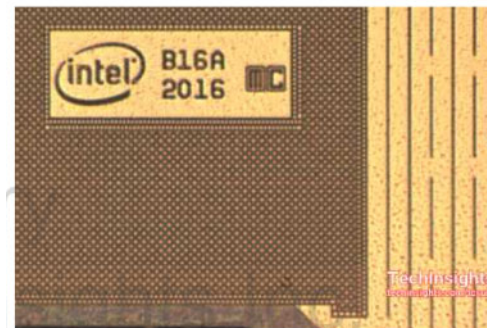
¹ Additional infringing Lenovo devices sold or offered for sale by T-Mobile, including at least Motorola G Pure, Moto G Play, Moto G7 Play, Moto G Fast devices.

On information and belief, Lenovo Moto G Power mobile phones contain a Micron MT29VZZZAD8QKSL-046 multi-chip module with LPDDR4 SDRAM (Z11N die), 3D NAND Flash (B16A die), and eMMC controller (PS8226 die).

A 3D NAND flash array is a cubic memory array.

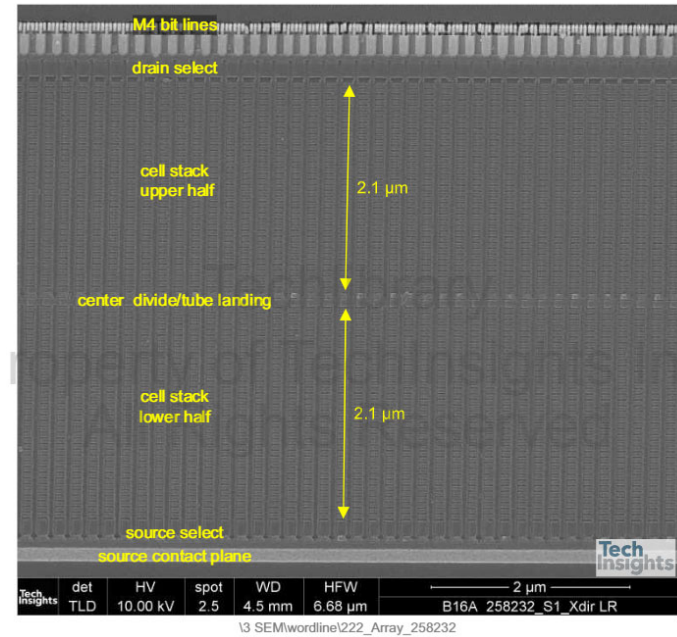
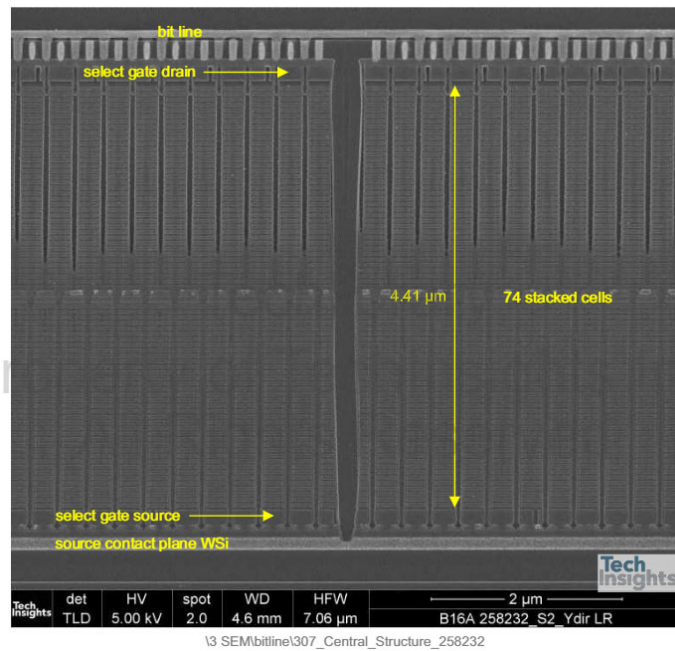


\\2 Package_and_Die_Photos\X-rays_and_Optical\29F01T2ANCH2_B16A_256107_Oriented



\\2 Package_and_Die_Photos\X-rays_and_Optical\29F01T2ANCH2_B16A_256107_DieMrk-50XRotated

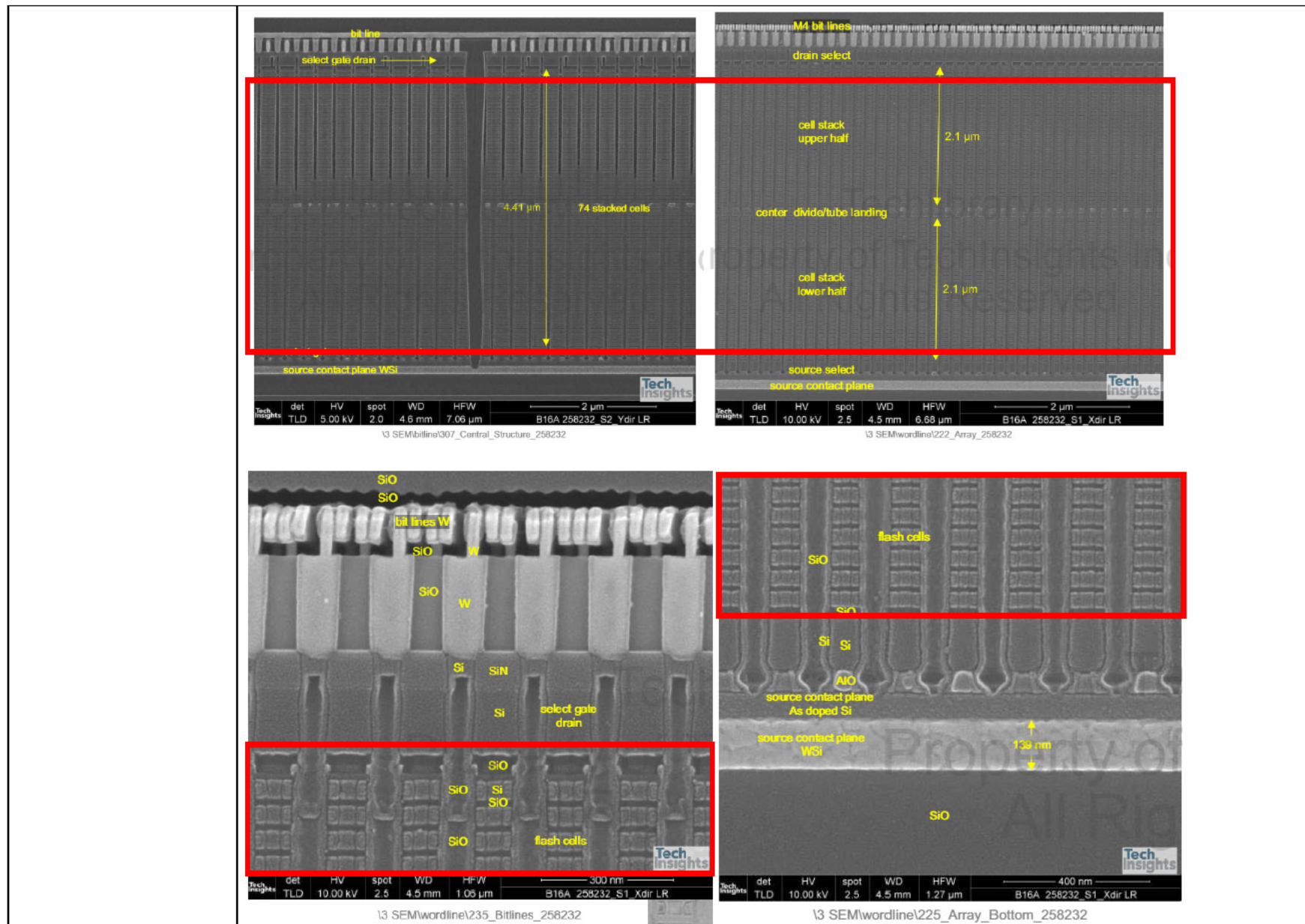
Techinsights, “Intel 29F01T2ANCH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018

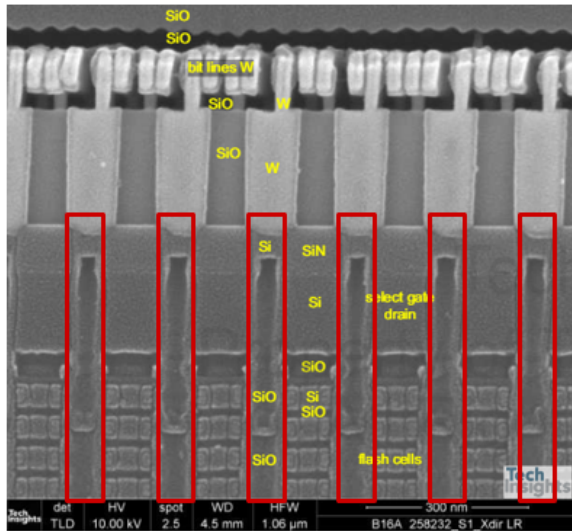
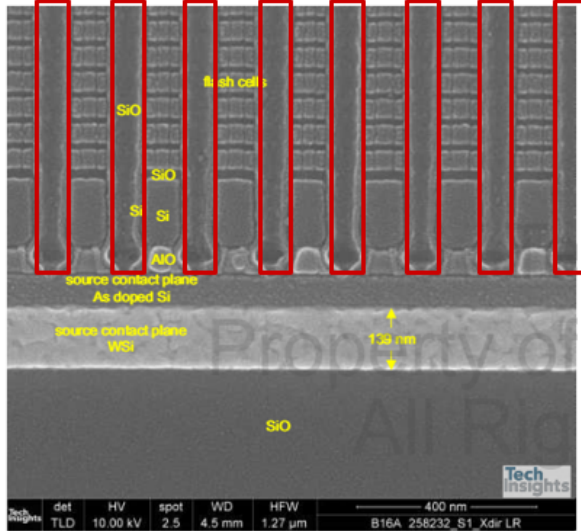


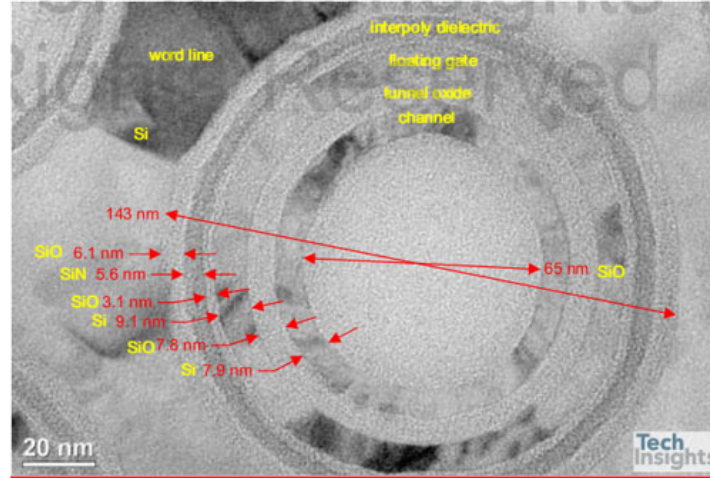
Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018

a plurality of horizontal select lines;

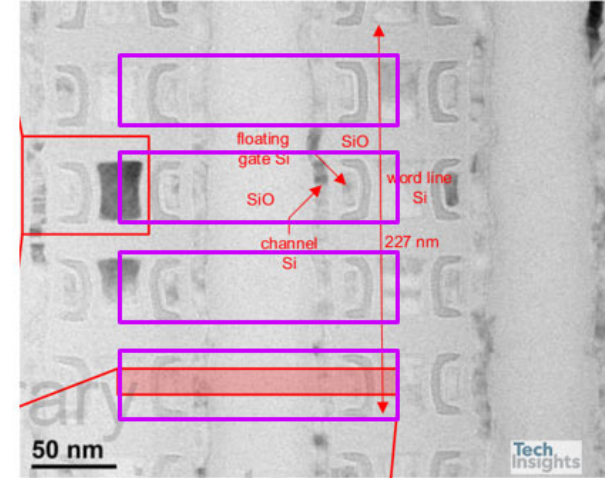
The 3D NAND Flash array has a plurality of wordlines, which are horizontal select lines.



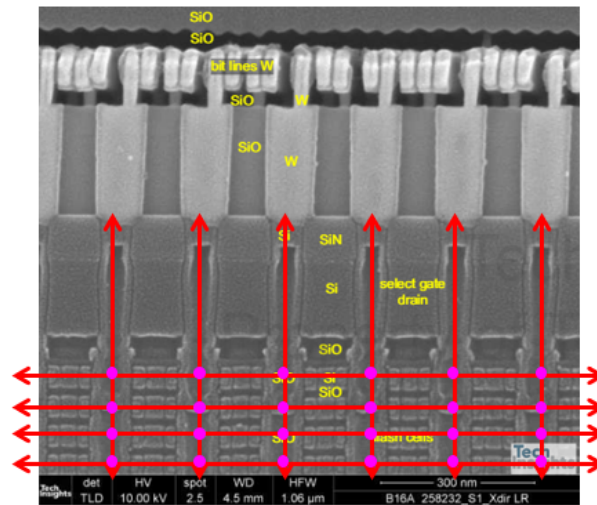
	<p>Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018</p>
<p>a plurality of vertical select lines;</p>	<p>The 3D NAND Flash array has a plurality of vertical select lines.</p> <div style="display: flex; justify-content: space-around;">   </div> <p>Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018</p>
<p>a plurality of memory cells, each memory cell adjacent to a horizontal select line and adjacent to a vertical select line; and</p>	<p>The 3D NAND Flash array has a plurality of floating gate memory cells, each memory cell adjacent to a horizontal select line and adjacent to a vertical select line.</p>



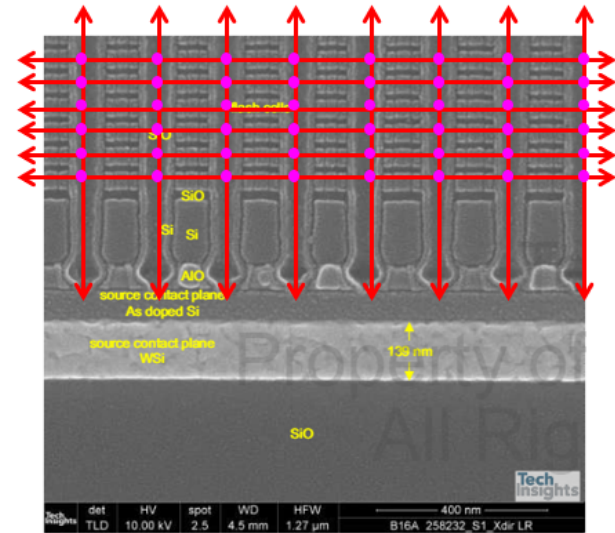
I4 TEM/bevel/cells near middle 130k_257788



I4 TEM/wordline/cells e 64k 2_257787



I3 SEM/wordline/235_Bitlines_258232

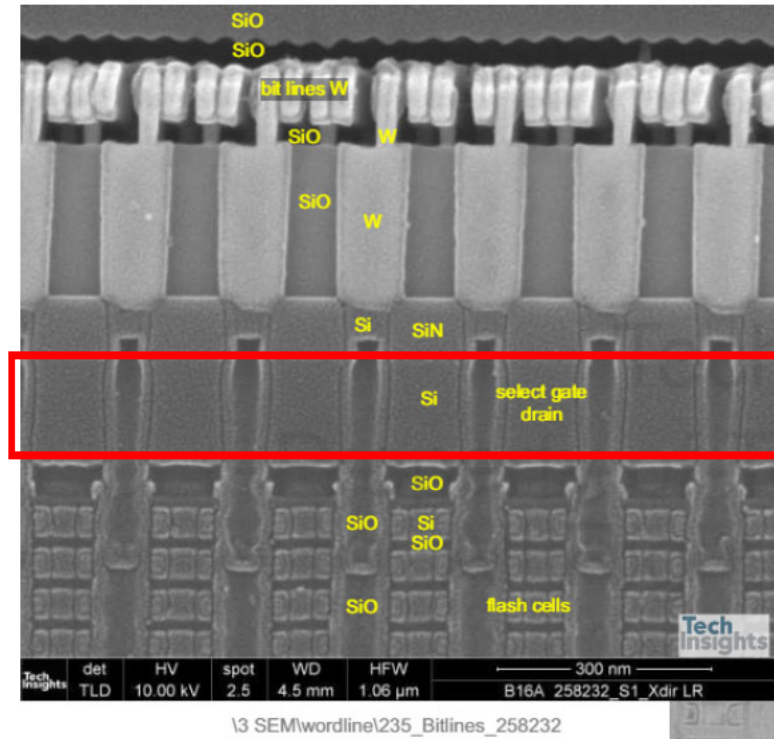


I3 SEM/wordline/225_Array_Bottom_258232

Techinsights, "Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash", report AME-1707-801.pdf, March 2018

at least one switching element disposed on top of at least one of the plurality of vertical select lines;

The 3D NAND Flash array has at least one switching element (select gate drain) disposed on top of at least one of the plurality of vertical select lines.

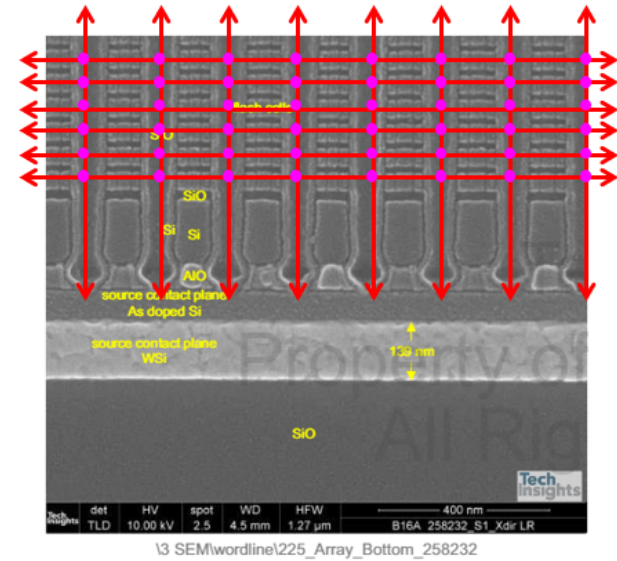
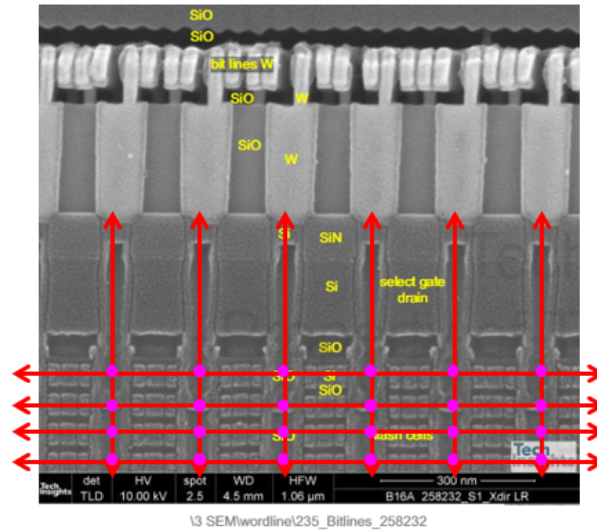


Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018

wherein the plurality of memory cells are arranged to form planes of horizontal select lines and planes of vertical select lines orthogonal to each other.

The 3D NAND Flash array has the plurality of memory cells arranged to form planes of horizontal select lines and planes of vertical select lines orthogonal to each other.

orthogonal to each other.



Techinsights, “Intel 29F01T2ANCTH2 64-Layer 256Gb 3D NAND Flash”, report AME-1707-801.pdf, March 2018